V_{DSS} 40 V
I_D 79 A
$R_{DS(ON)}$ 4.2 mΩ

Features

Uses advanced SGT technology
Extremely low on-resistance RDS(on)
Excellent gate charge x RDS(on) product(FOM)

Application

Motor control and drive
Battery management
DC/DC

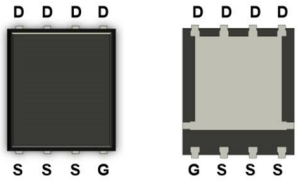
GK xxx
S004N04

LOGO GK xxx CODE

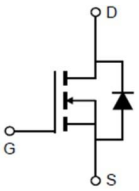
S004N04

RDS(ON) VDSS

PDFN5X6-8L top&bottom view



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous drain current T_c=25℃（Silicon limit） T_c=100℃（Silicon limit）	I_D	 79 50	A
Pulsed Drain Current	I_{DM}	300	A
Maximum Power Dissipation	P_d	45	W
Single pulse avalanche energy	E_{AS}	182	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R_{thJC}	2.3	℃/W
Thermal Resistance,Junction-to-Ambient	R_{thJA}	50	

Electrical Characteristics (T_J=25℃unless otherwise noted)

Parameter	Symbol	Condition	min	typ	max	Unit
Static Characteristic						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250uA	40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=VGS, I_D=250uA	1.2	1.7	2.5	
Zero gate voltage drain current	I_{DSS}	V_{DS}=40V,V_{GS}=0V	-	-	1.0	μA
Gate-source leakage current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Drain-source on-state resistance	$R_{DS(on)}$	I_D=40A,V_{GS}=10V	-	4.2	5.2	mΩ
Dynamic Characteristic						
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V, f=1MHz	-	868	-	pF
Output Capacitance	C_{oss}		-	473	-	
Reverse Transfer Capacitance	C_{rss}		-	9	-	
Gate resistance	Rg	f=1MHz	-	5	-	Ω
Gate Total Charge	Q_G	V_{DS}=20V,I_D=20A, V_{GS}=10V	-	18	-	nC
Gate-Source charge	Q_{gs}		-	3	-	
Gate-Drain charge	Q_{gd}		-	4	-	
Turn-on delay time	$t_{d(on)}$	V_{GS}=10V, V_{DS}=20V, I_D=20A, R_{REN}=6Ω	-	5	-	ns
Rise time	t_r		-	9	-	
Turn-off delay time	$t_{d(off)}$		-	23	-	
Fall time	t_f		-	15	-	
Body Diode Characteristic						
Diode Forward Voltage	V_{SD}	VGS=0V,IS=65A	-	-	1.2	v
Reverse Recovery Time	t_{rr}	I_F =65A di/dt = 100A/μs	-	-	23	ns
Reverse Recovery Charge	Q_{rr}		-	-	62	nC

RATING AND CHARACTERISTIC CURVES

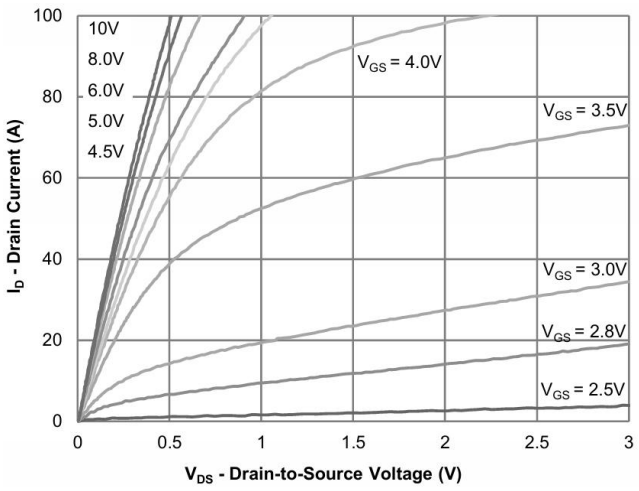


Figure 1: Output Characteristics

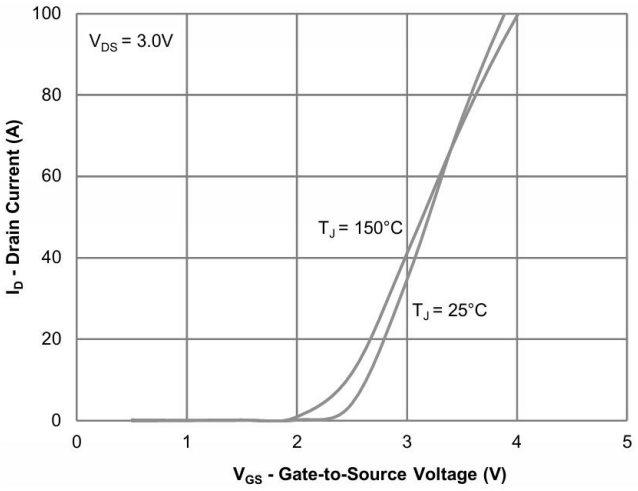


Figure 2: Transfer Characteristics

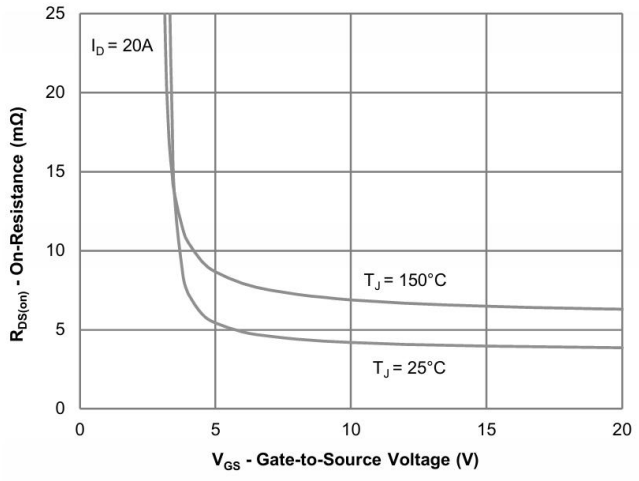


Figure 3: On-Resistance vs. Gate-Source Voltage

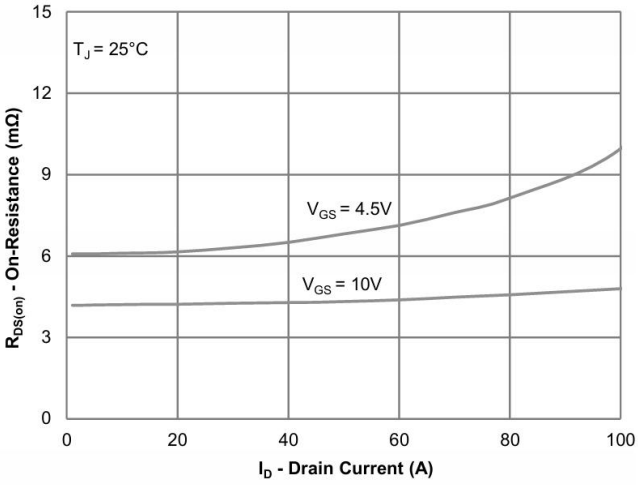


Figure 4: On-Resistance vs. Drain Current and Gate Voltage

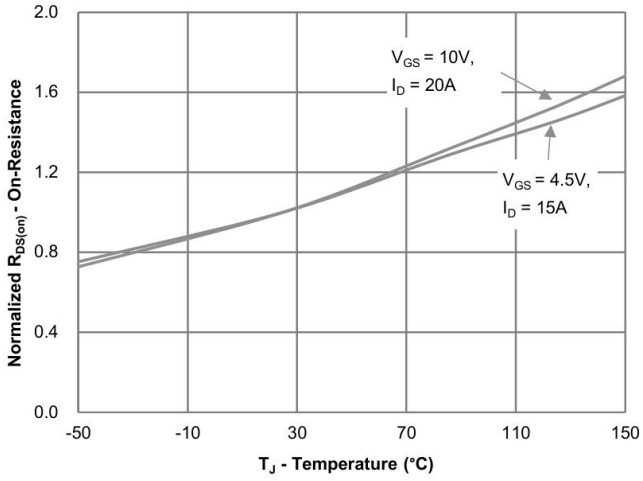


Figure 5: On-Resistance vs. Junction Temperature

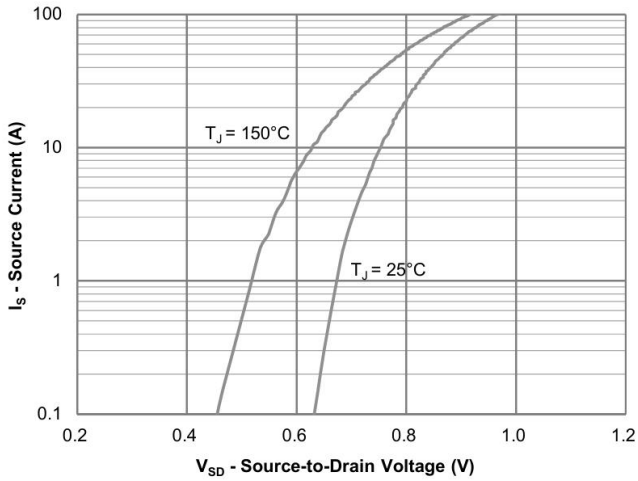


Figure 6: Source-Drain Diode Forward Voltage

RATING AND CHARACTERISTIC CURVES

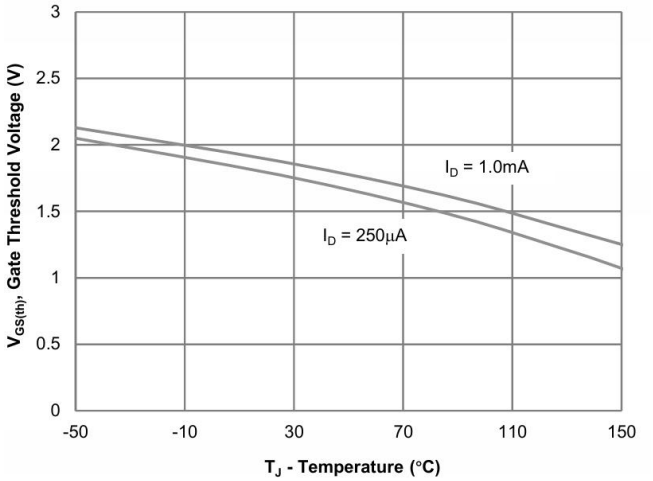


Figure 7: Gate Threshold Variation vs. Junction Temperature

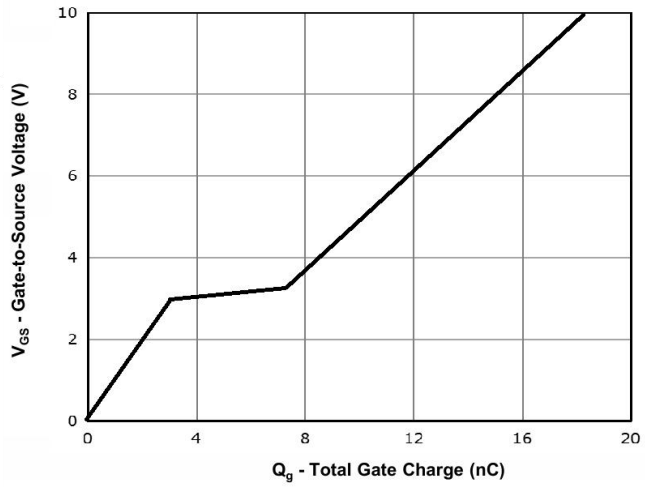


Figure 8: Gate Charge Characteristics

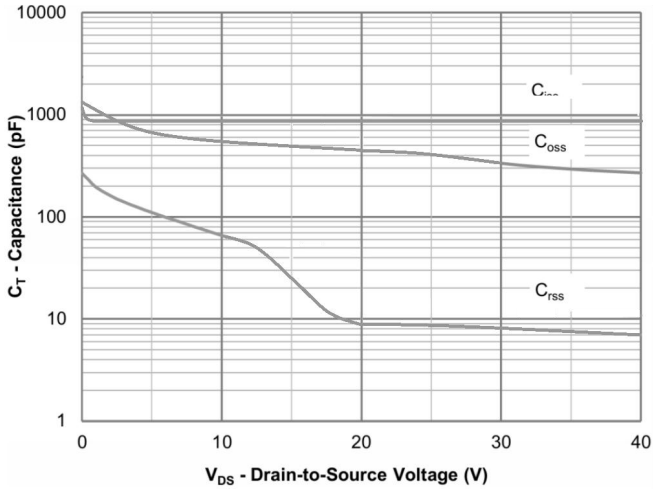


Figure 9: Capacitance Characteristics

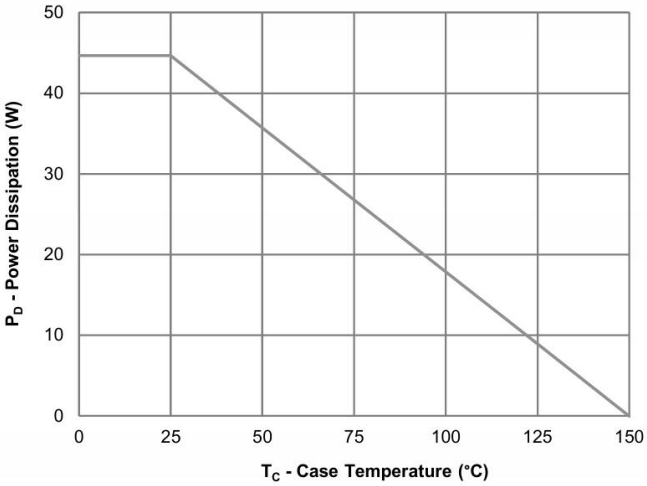


Figure 10: Power Derating

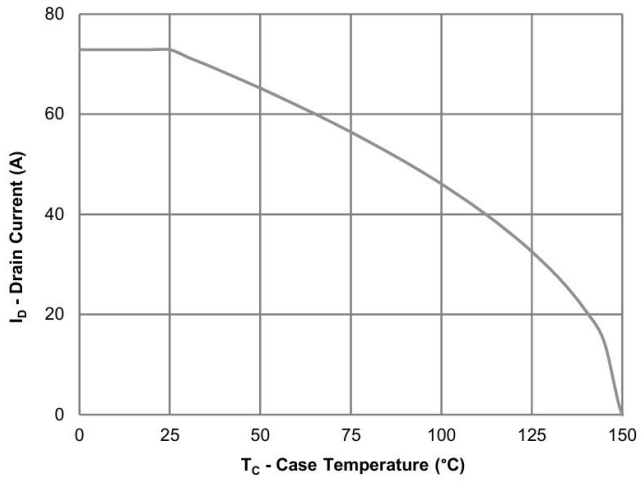


Figure 11: Current Derating

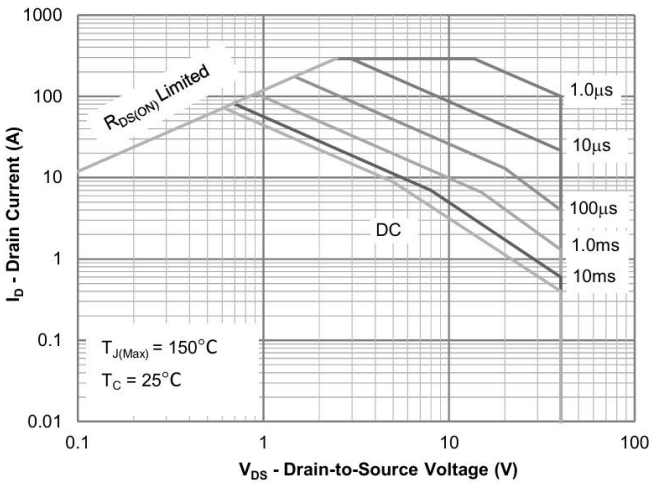


Figure 12: Safe Operating Area

RATING AND CHARACTERISTIC CURVES

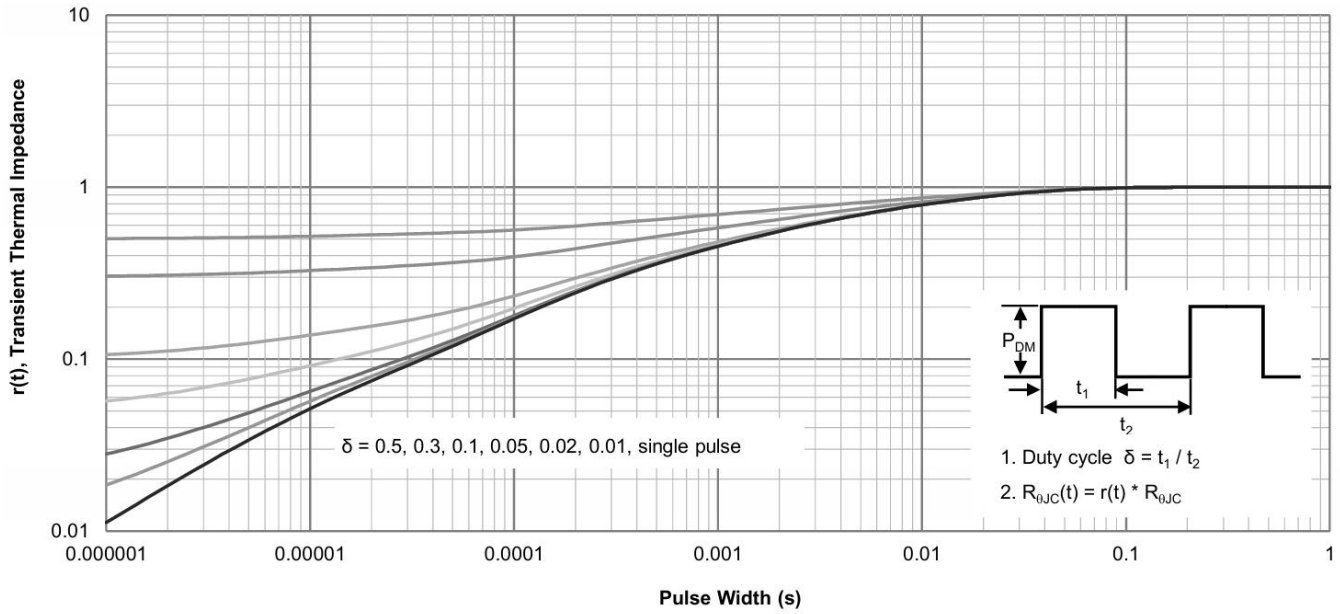
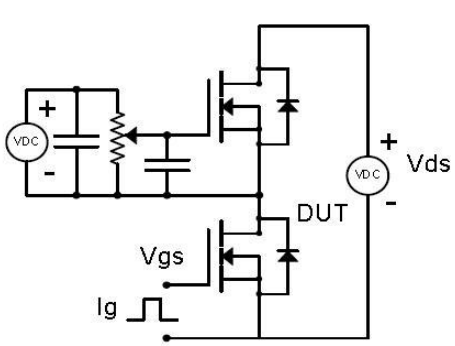
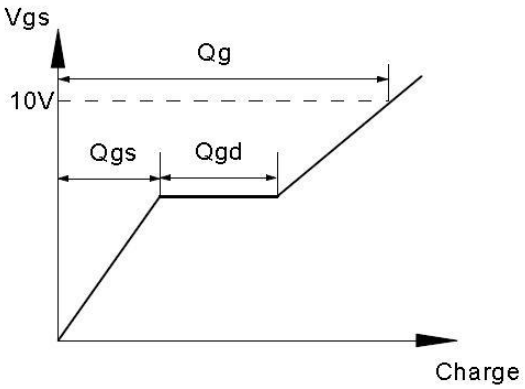


Figure 13: Normalized Maximum Transient Thermal Impedance

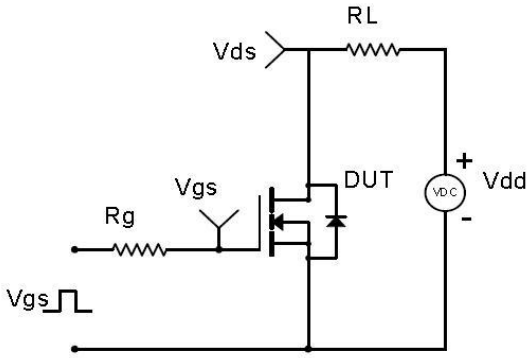
Test Circuit & Waveform

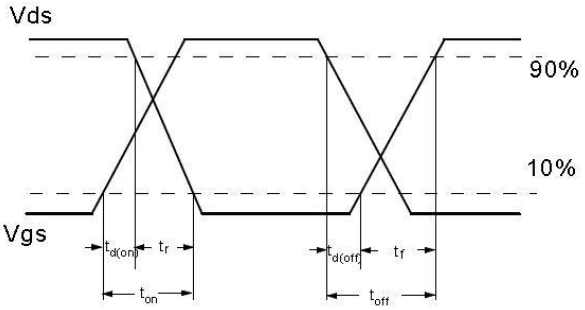
Gate Charge Test Circuit & Waveform



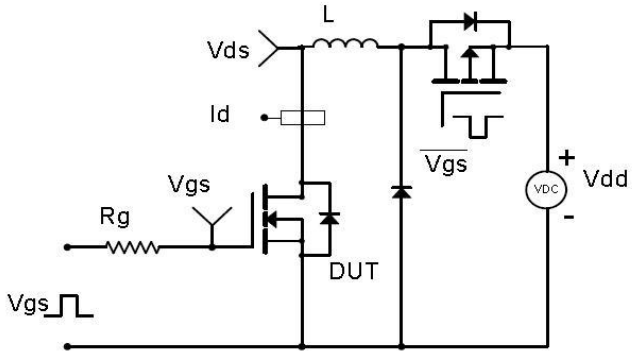


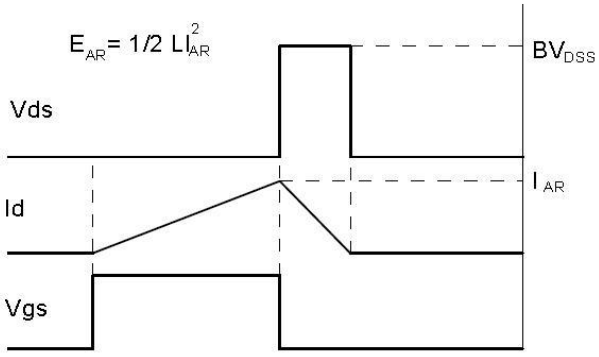
Resistive Switching Test Circuit & Waveforms



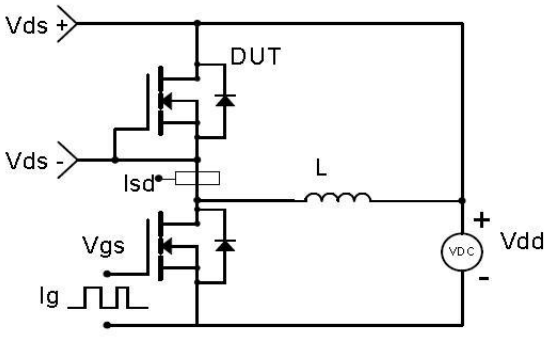


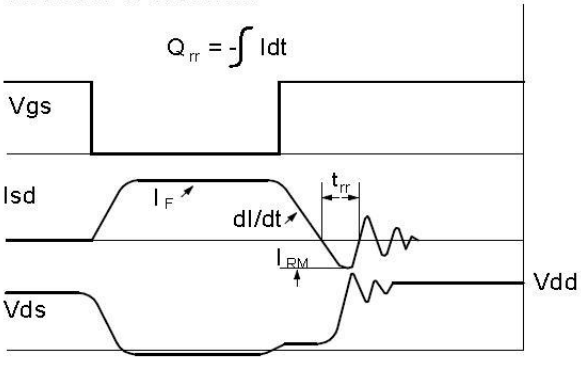
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms





Diode Recovery Test Circuit & Waveforms

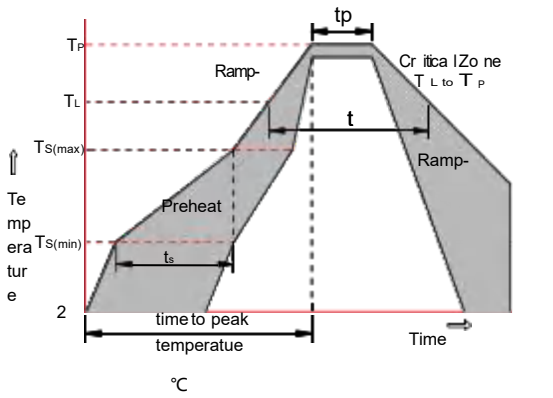




Soldering parameters

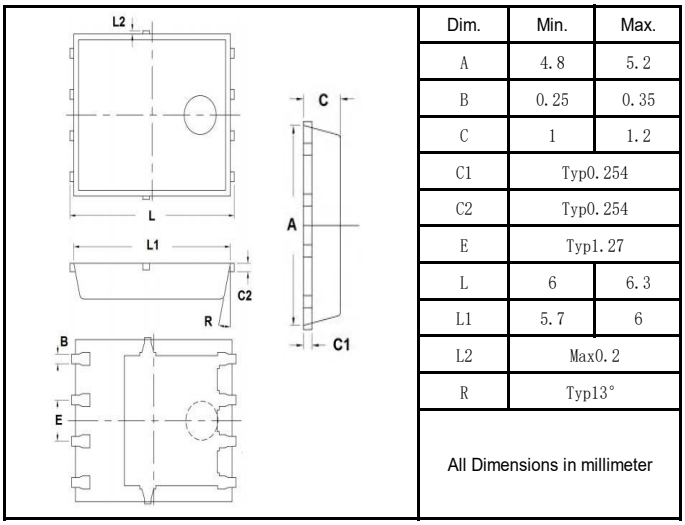
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition



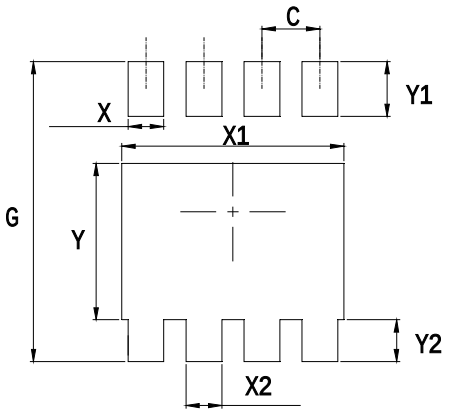
Package Dimensions & Suggested Pad Layout

PDFN5*6



Dim.	Min.	Max.
A	4.8	5.2
B	0.25	0.35
C	1	1.2
C1	Typ0.254	
C2	Typ0.254	
E	Typ1.27	
L	6	6.3
L1	5.7	6
L2	Max0.2	
R	Typ13°	

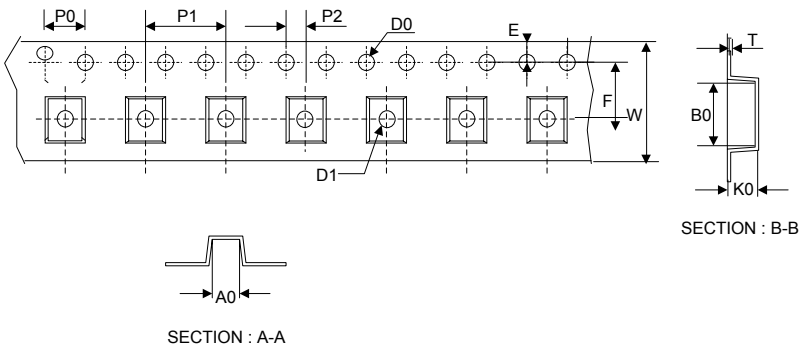
All Dimensions in millimeter



Dimensions	Value (in mm)
C	1.27
G	6.45
X	0.62
X1	4.50
X2	0.62
Y	3.70
Y1	1.05
Y2	0.80

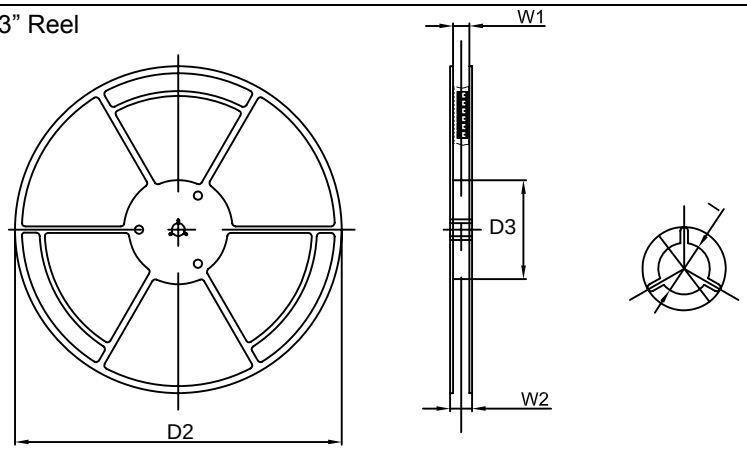
Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.55±0.20
E	1.75±0.20
F	5.50±0.20
W	12.00±0.20
A0	6.60±0.20
B0	5.70±0.20
K0	1.30±0.20
T	0.20±0.20

13” Reel



D2	330.0±5.0
D3	100.0±4.0
W1	12.0±5.0
W2	14.0±5.0
I	13.0±2.0

Quantity: 5000PCS